

SM73306 CMOS Rail-to-Rail Input and Output Operational Amplifier

Check for Samples: SM73306

FEATURES

(Typical Unless Otherwise Noted)

- **Renewable Energy Grade**
- Rail-to-Rail Input Common-Mode Voltage • Range, Specified Over Temperature
- Rail-to-Rail Output Swing Within 20 mV of • Supply Rail, 100 kΩ Load
- **Operates from 5V to 15V Supply** .
- Excellent CMRR and PSRR 8 dB
- Ultra Low Input Current 150 fA
- High Voltage Gain ($R_L = 100 \text{ k}\Omega$) 120 dB
- Low Supply Current (@ $V_S = 5V$) 500 µA/Amplifier
- Low Offset Voltage Drift 1.0 µV/°C

APPLICATIONS

- Automotive Transducer Amplifier
- **Pressure Sensor**
- **Oxygen Sensor**
- **Temperature Sensor**
- Speed Sensor

CONNECTION DIAGRAM

DESCRIPTION

The SM73306 amplifier was specifically developed for single supply applications that operate from -40°C to +125°C. This wide temperature range makes it wellsuited for photovoltaic systems. A unique design topology enables the SM73306 common-mode voltage range to accommodate input signals beyond the rails. This eliminates non-linear output errors due to input signals exceeding a traditionally limited common-mode voltage range. The SM73306 signal range has a high CMRR of 82 dB for excellent accuracy in non-inverting circuit configurations.

The SM73306 rail-to-rail input is complemented by rail-to-rail output swing. This assures maximum dynamic signal range which is particularly important in 5V systems.

Ultra-low input current of 150 fA and 120 dB open loop gain provide high accuracy and direct interfacing with high impedance sources.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. All trademarks are the property of their respective owners.

SM73306

SNOSB99B-JUNE 2011-REVISED APRIL 2013

TEXAS INSTRUMENTS

www.ti.com



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings (1)(2)

ESD Tolerance ⁽³⁾	2000V
Differential Input Voltage	±Supply Voltage
Voltage at Input/Output Pin	(V⁺) + 0.3V, (V⁻) − 0.3V
Supply Voltage $(V^+ - V^-)$	16V
Current at Input Pin	±5 mA
Current at Output Pin ⁽⁴⁾	±30 mA
Current at Power Supply Pin	40 mA
Lead Temp. (Soldering, 10 sec.)	260°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature ⁽⁵⁾	150°C

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional. For specifications and the test conditions, see the Electrical Characteristics.

(2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

- (3) Human body model, 1.5 k Ω in series with 100 pF.
- (4) Applies to both single-supply and split-supply operation. Continuous short operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature at 150°C. Output currents in excess of ±30 mA over long term may adversely affect reliability.

(5) The maximum power dissipation is a function of $T_{J(max)}$, θ_{JA} and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(max)} - T_A)/\theta_{JA}$. All numbers apply for packages soldered directly into a PC board.

Operating Conditions ⁽¹⁾

Supply Voltage	2.5V ≤ V ⁺ ≤ 15.5V
Junction Temperature Range	−40°C ≤ T _J ≤ +125°C
Thermal Resistance (θ _{JA})	171°C/W

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional. For specifications and the test conditions, see the Electrical Characteristics.

DC Electrical Characteristics

Unless otherwise specified, all limits specified for $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V_O = V^+/2$ and $R_L > 1 \text{ M}\Omega$. Boldface limits apply at the temperature extremes

Symbol	Parameter	Conditions	Тур ⁽¹⁾	Limit ⁽²⁾	Units
V _{OS}	Input Offset Voltage		0.11	6.0	mV
				6.8	max
TCV _{OS}	Input Offset Voltage Average Drift		1.0		μV/°C
I _B	Input Bias Current	(3)	0.15	200	pA max
los	Input Offset Current	(3)	0.075	100	pA max
R _{IN}	Input Resistance		>10		Tera Ω
C _{IN}	Common-Mode Input Capacitance		3		pF
CMRR	Common-Mode	$0V \le V_{CM} \le 15V$	82	63	dB
Reje	Rejection Ratio	V ⁺ = 15V		58	min
		$0V \le V_{CM} \le 5V$	82	63	
				58	
+PSRR	Positive Power Supply Rejection Ratio	$5V \le V^+ \le 15V$,	82	63	dB
		V _O = 2.5V		58	min

(1) Typical Values represent the most likely parametric norm.

(2) All limits are specified by testing or statistical analysis.

(3) Limits are dictated by tester limits and not device performance. Actual performance is reflected in the typical value.



SNOSB99B-JUNE 2011-REVISED APRIL 2013

www.ti.com

DC Electrical Characteristics (continued)

Unless otherwise specified, all limits specified for $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V_O = V^+/2$ and $R_L > 1$ M Ω . Boldface limits apply at the temperature extremes

Symbol	Parameter	Conditions	Тур ⁽¹⁾	Limit ⁽²⁾	Units
-PSRR	Negative Power Supply	$0V \leq V^{-} \leq -10V,$	82	63	dB
	Rejection Ratio	$V_{O} = 2.5V$		58	min
V _{CM}	Input Common-Mode	V ⁺ = 5V and 15V	V ⁻ -0.3	-0.25	V
Vol	Voltage Range	For CMRR ≥ 50 dB		0	max
			V ⁺ + 0.3	V ⁺ + 0.25	V
				V*	min
A _V	Large Signal Voltage Gain	$R_L = 2 k\Omega$: Sourcing	300		V/mV
		(4) Sinking	40		min
Vo	Output Swing	$V^+ = 5V$ $R_L = 2 k\Omega$ to $V^+/2$	4.9	4.8	V
				4.7	min
			0.1	0.18	V
				0.24	max
		V ⁺ = 5V	4.7	4.5	V
		$R_{L} = 600\Omega$ to V ⁺ /2		4.24	min
			0.3	0.5	V
				0.65	max
		$V^+ = 15V$ $R_L = 2 k\Omega$ to V ⁺ /2	14.7	14.4	V
				14.0	min
			0.16	0.35	V
				0.5	max
		$V^{+} = 15V$ R _L = 600Ω to V ⁺ /2	14.1	13.4	V
				13.0	min
			0.5	1.0	V
				1.5	max
I _{SC}	Output Short Circuit Current	Sourcing, $V_0 = 0V$	25	16	
	V ⁺ = 5V			10	
		Sinking, $V_0 = 5V$	22	11	
				8	mA
I _{SC}	Output Short Circuit Current V ⁺ = 15V	t Current Sourcing, V _O = 0V	30	28	min
				20	
		Sinking, $V_O = 5V^{(5)}$	30	30	
				22	
I _S	Supply Current	Current $V^+ = +5V, V_0 = V^+/2$	1.0	1.75	mA
				2.1	max
		$V^+ = +15V, V_0 = V^+/2$	1.3	1.95	mA
				2.3	max

(4) $V^+ = 15V$, $V_{CM} = 7.5V$ and R_L connected to 7.5V. For Sourcing tests, $7.5V \le V_O \le 11.5V$. For Sinking tests, $3.5V \le V_O \le 7.5V$. (5) Do not short circuit output to V⁺, when V⁺ is greater than 13V or reliability will be adversely affected.



AC Electrical Characteristics

Unless otherwise specified, all limits specified for $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V_O = V^+/2$ and $R_L > 1 \text{ M}\Omega$. Boldface limits apply at the temperature extremes

Symbol	Parameter	Conditions	Тур ⁽¹⁾	Limit ⁽²⁾	Units
SR	Slew Rate	(3)	1.3	0.7 0.5	Vµs min
GBW	Gain-Bandwidth Product	V ⁺ = 15V	1.5		MHz
φ _m	Phase Margin		50		Deg
G _m	Gain Margin		15		dB
	Amp-to-Amp Isolation	(4)	150		dB
e _n	Input-Referred Voltage Noise	F = 1 kHz $V_{CM} = 1 \text{ V}$	37		nV/√Hz
i _n	Input-Referred Current Noise	F = 1 kHz	0.06		pA√Hz
T.H.D.	Total Harmonic Distortion	$F = 1 \text{ kHz}, A_V = -2$ R _L = 10 kΩ, V _O = -4.1 V _{PP}	0.01		
			0.01		%

(1) Typical Values represent the most likely parametric norm.

(2)

All limits are specified by testing or statistical analysis. $V^+ = 15V$. Connected as voltage follower with 10V step input. Number specified is the slower of the positive and negative slew rates. Input referred, $V^+ = 15V$ and $R_L = 100 \text{ k}\Omega$ connected to 7.5V. Each amp excited in turn with 1 kHz to produce $V_0 = 12 \text{ V}_{PP}$. (3)

(4)





Typical Performance Characteristics

 V_{S} = +15V, Single Supply, T_{A} = 25°C unless otherwise specified













NSTRUMENTS

EXAS

= 3١

10

10k

5



= 5 kΩ

10.0

 $= 5 k \Omega$

10k

15V

٧_S =

R $= 5 k \Omega$

100k

R



FREQUENCY (Hz) Figure 19.

Figure 18.

10k

100k

3

8

www.ti.com

SNOSB99B-JUNE 2011-REVISED APRIL 2013



Typical Performance Characteristics (continued)





GAIN (dB)

















 V_S = +15V, Single Supply, T_A = 25°C unless otherwise specified



TIME $(1 \mu s/DIV)$ Figure 36.

1 μs







Figure 37.

1~

ĩĩ



Typical Performance Characteristics (continued)



Figure 38.











TIME $(1 \mu s/DIV)$ Figure 39.



TIME (1μs/DIV) Figure 41.



TIME $(1 \mu s/DIV)$ Figure 43.

SNOSB99B-JUNE 2011-REVISED APRIL 2013



Figure 48.



TIME $(1 \mu s/DIV)$ Figure 45.



TIME $(1 \mu s/DIV)$ Figure 47.





SNOSB99B-JUNE 2011-REVISED APRIL 2013









SNOSB99B-JUNE 2011-REVISED APRIL 2013

www.ti.com

APPLICATION HINTS

INPUT COMMON-MODE VOLTAGE RANGE

Unlike Bi-FET amplifier designs, the SM73306 does not exhibit phase inversion when an input voltage exceeds the negative supply voltage. Figure 54 shows an input voltage exceeding both supplies with no resulting phase inversion on the output.





The absolute maximum input voltage is 300 mV beyond either supply rail at room temperature. Voltages greatly exceeding this absolute maximum rating, as in Figure 55, can cause excessive current to flow in or out of the input pins possibly affecting reliability.



Figure 55. A ±7.5V Input Signal Greatly Exceeds the 5V Supply in Figure 56 Causing No Phase Inversion Due to R_I

Applications that exceed this rating must externally limit the maximum input current to ± 5 mA with an input resistor (R_I) as shown in Figure 56.



Figure 56. R_I Input Current Protection for Voltages Exceeding the Supply Voltages

RAIL-TO-RAIL OUTPUT

The approximate output resistance of the SM73306 is 110Ω sourcing and 80Ω sinking at V_s = 5V. Using the calculated output resistance, maximum output voltage swing can be esitmated as a function of load.



COMPENSATING FOR INPUT CAPACITANCE

It is quite common to use large values of feedback resistance for amplifiers with ultra-low input current, like the SM73306.

Although the SM73306 is highly stable over a wide range of operating conditions, certain precautions must be met to achieve the desired pulse response when a large feedback resistor is used. Large feedback resistors with even small values of input capacitance, due to transducers, photodiodes, and circuit board parasitics, reduce phase margins.

When high input impedances are demanded, guarding of the SM73306 is suggested. Guarding input lines will not only reduce leakage, but lowers stray input capacitance as well. (See PRINTED-CIRCUIT-BOARD LAYOUT FOR HIGH-IMPEDANCE WORK).

The effect of input capacitance can be compensated for by adding a capacitor, C_f , around the feedback resistors (as in Figure 54) such that:

$$\frac{1}{2\pi\mathsf{R}_{1}\mathsf{C}_{\mathsf{IN}}} \ge \frac{1}{2\pi\mathsf{R}_{2}\mathsf{C}_{\mathsf{f}}} \tag{1}$$

or

$$R_1 C_{IN} \le R_2 C_f$$

(2)

Since it is often difficult to know the exact value of C_{IN} , C_f can be experimentally adjusted so that the desired pulse response is achieved.

Figure 57. Cancelling the Effect of Input Capacitance

CAPACITIVE LOAD TOLERANCE

All rail-to-rail output swing operational amplifiers have voltage gain in the output stage. A compensation capacitor is normally included in this integrator stage. The frequency location of the dominant pole is affected by the resistive load on the amplifier. Capacitive load driving capability can be optimized by using an appropriate resistive load in parallel with the capacitive load (see Typical Performance Characteristics).

Direct capacitive loading will reduce the phase margin of many op-amps. A pole in the feedback loop is created by the combination of the op-amp's output impedance and the capacitive load. This pole induces phase lag at the unity-gain crossover frequency of the amplifier resulting in either an oscillatory or underdamped pulse response. With a few external components, op amps can easily indirectly drive capacitive loads, as shown in Figure 58.

 V_{IN}

Figure 58. SM73306 Noninverting Amplifier, Compensated to Handle Capacitive Loads



SNOSB99B-JUNE 2011-REVISED APRIL 2013



PRINTED-CIRCUIT-BOARD LAYOUT FOR HIGH-IMPEDANCE WORK

It is generally recognized that any circuit which must operate with less than 1000 pA of leakage current requires special layout of the PC board. When one wishes to take advantage of the ultra-low bias current of the SM73306, typically 150 fA, it is essential to have an excellent layout. Fortunately, the techniques of obtaining low leakages are quite simple. First, the user must not ignore the surface leakage of the PC board, even though it may sometimes appear acceptably low, because under conditions of high humidity or dust or contamination, the surface leakage will be appreciable.

To minimize the effect of any surface leakage, lay out a ring of foil completely surrounding the SM73306's inputs and the terminals of components connected to the op-amp's inputs, as in Figure 59. To have a significant effect, guard rings should be placed on both the top and bottom of the PC board. This PC foil must then be connected to a voltage which is at the same voltage as the amplifier inputs, since no leakage current can flow between two points at the same potential. For example, a PC board trace-to-pad resistance of $10^{12}\Omega$, which is normally considered a very large resistance, could leak 5 pA if the trace were a 5V bus adjacent to the pad of the input.

This would cause a 33 times degradation from the SM73306's actual performance. If a guard ring is used and held within 5 mV of the inputs, then the same resistance of $10^{12}\Omega$ will only cause 0.05 pA of leakage current. See Figure 60 for typical connections of guard rings for standard op-amp configurations.



Figure 59. Examples of Guard Ring in PC Board Layout









Application Circuits



Where: $V_0 = V_1 + V_2 - V_3 - V_4$ ($V_1 + V_2 \ge (V_3 + V_4)$ to keep $V_0 > 0V_{DC}$





For

 $\frac{\text{R1}}{\text{R2}}=\frac{\text{R4}}{\text{R3}}$

(CMRR depends on this resistor ratio match)

$$V_0 = 1 + \frac{R4}{R3}(V_2 - V_1)$$

As shown: $V_0 = 2(V_2 - V_1)$

Figure 62. High Input Z, DC Differential Amplifier



Figure 63. Photo Voltaic-Cell Amplifier



SNOSB99B-JUNE 2011-REVISED APRIL 2013



If R1 = R5, R3 = R6, and R4 = R7; then

$$\frac{V_{OUT}}{V_{IN}} = \frac{R2 + 2R1}{R2} \times \frac{R4}{R3}$$

 $\therefore A_V \approx 100$ for circuit shown (R₂ = 9.3k).





Figure 65. Rail-to-Rail Single Supply Low Pass Filter

This low-pass filter circuit can be used as an anti-aliasing filter with the same supply as the A/D converter. Filter designs can also take advantage of the SM73306 ultra-low input current. The ultra-low input current yields negligible offset error even when large value resistors are used. This in turn allows the use of smaller valued capacitors which take less board space and cost less.



Figure 66. Low Voltage Peak Detector with Rail-to-Rail Peak Capture Range

Dielectric absorption and leakage is minimized by using a polystyrene or polypropylene hold capacitor. The droop rate is primarily determined by the value of C_H and diode leakage current. Select low-leakage current diodes to minimize drooping.



SNOSB99B-JUNE 2011-REVISED APRIL 2013



Figure 67. Pressure Sensor

In a manifold absolute pressure sensor application, a strain gauge is mounted on the intake manifold in the engine unit. Manifold pressure causes the sensing resistors, R1, R2, R3 and R4 to change. The resistors change in a way such that R2 and R4 increase by the same amount R1 and R3 decrease. This causes a differential voltage between the input of the amplifier. The gain of the amplifier is adjusted by R_f .

SNOSB99B-JUNE 2011-REVISED APRIL 2013

Changes from Revision A (April 2013) to Revision A



Page

www.ti.com

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications		
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive	
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications	
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers	
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps	
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy	
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial	
Interface	interface.ti.com	Medical	www.ti.com/medical	
Logic	logic.ti.com	Security	www.ti.com/security	
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense	
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video	
RFID	www.ti-rfid.com			
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com	
Wireless Connectivity	www.ti.com/wirelessconnectivity			

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2013, Texas Instruments Incorporated